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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 4x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFBGA
Supplier Device Package	48-BGA (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg825f8-bga48t

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divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 μ DMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32TG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32TG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32TG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 Inter-Integrated Circuit Interface (I2C)

The I^2C module provides an interface between the MCU and a serial I^2C -bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s. Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I^2C module, allows both fine-grained control of the transmission process and close to automatic transfers. Automatic recognition of slave addresses is provided in all energy modes.

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}C$ and $V_{DD}=3.0$ V, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 9) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 9).

Symbol	Parameter	Condition	Min	Тур	Max	Unit
T _{STG}	Storage tempera- ture range		-40		150 ¹	°C
Τ _S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V _{DDMAX}	External main sup- ply voltage		0		3.8	V
V _{IOPIN}	Voltage on any I/O pin		-0.3		V _{DD} +0.3	V

Table 3.1. Absolute Maximum Ratings

¹Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Тур	Max	Unit
T _{AMB}	Ambient temperature range	-40		85	°C
V _{DDOP}	Operating supply voltage	1.98		3.8	V
f _{APB}	Internal APB clock frequency			32	MHz
f _{AHB}	Internal AHB clock frequency			32	MHz

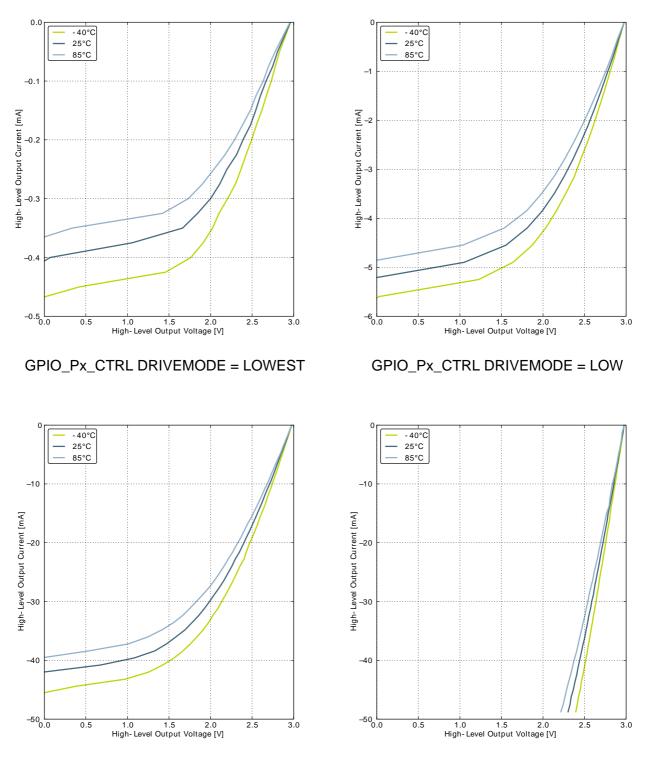
3.4 Current Consumption

Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		32 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V		157		μΑ/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		150	170	µA/ MHz
	EM0 current. No prescaling. Running	21 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		153	172	µA/ MHz
I _{EM0}	prime number cal- culation code from Flash. (Production	14 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		155	175	µA/ MHz
	test condition = 14 MHz)	11 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		157	178	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		162	183	μΑ/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		200	240	μΑ/ MHz
		32 MHz HFXO, all peripheral clocks disabled, V_{DD} = 3.0 V		53		µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		51	57	µA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		55	59	µA/ MHz
I _{EM1}	EM1 current (Pro- duction test condi- tion = 14 MHz)	14 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		56	61	µA/ MHz
	,	11 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		58	63	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		63	68	µA/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD} = 3.0 V		100	122	µA/ MHz
	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =25°C		1.0	1.2	μA
I _{EM2}		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD} = 3.0 V, T_{AMB} =85°C		2.4	5.0	μA
Inno	EM3 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.59	1.0	μA
I _{EM3}		V _{DD} = 3.0 V, T _{AMB} =85°C		2.0	4.5	μA
I _{EM4}	EM4 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.02	0.055	μA
•⊂IVI4		V _{DD} = 3.0 V, T _{AMB} =85°C		0.25	0.70	μA



Figure 3.7. Typical High-Level Output Current, 3V Supply Voltage

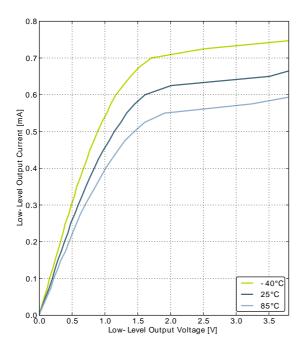


GPIO_Px_CTRL DRIVEMODE = STANDARD

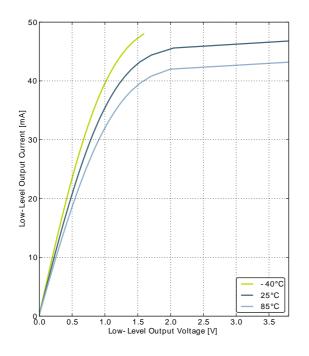
GPIO_Px_CTRL DRIVEMODE = HIGH



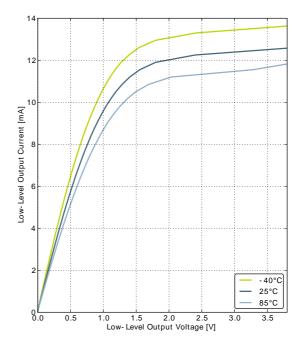
Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage



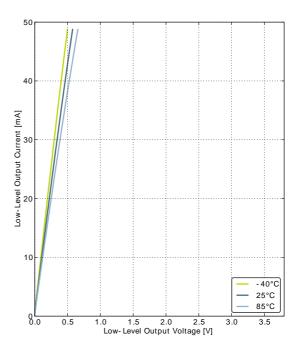
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.13. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

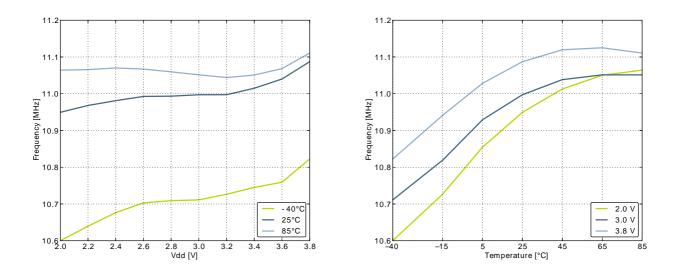


Figure 3.14. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature

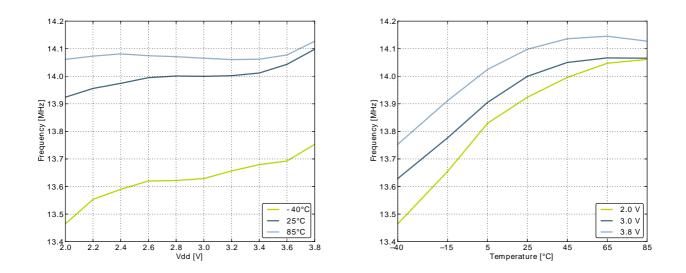
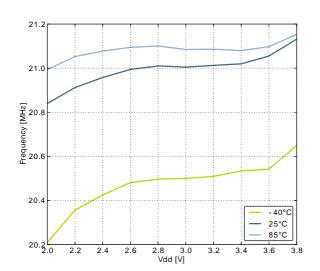
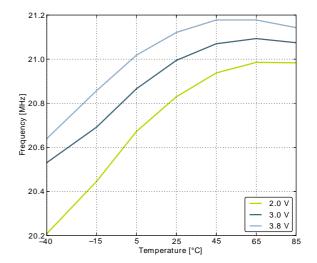


Figure 3.15. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature







Symbol	Parameter	Condition	Min	Тур	Max	Unit
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference		69		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		70		dB
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		64		dB
		1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
SINAD _{ADC}	SIgnal-to-Noise And Distortion-ratio	1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		68		dB
SINADADC	(SINAD)	200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, V _{DD} reference	62	68		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		69		dB
SFDR _{ADC}	Spurious-Free Dy- namic Range (SF-	1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		64		dBc
	DR)	1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differen- tial, V _{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		75		dBc
		1 MSamples/s, 12 bit, differen- tial, 5V reference		69		dBc
		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V _{DD} reference	68	76		dBc
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differ- ential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference		79		dBc
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		79		dBc
M	Offect veltage	After calibration, single ended	-4	0.3	4	mV
VADCOFFSET	Offset voltage	After calibration, differential		0.3		mV
				-1.92		mV/°C
TGRAD _{ADCTH}	Thermometer out- put gradient			-6.3		ADC Codes/ °C
DNL _{ADC}	Differential non-lin- earity (DNL)	V _{DD} = 3.0 V, external 2.5V reference	-1	±0.7	4	LSB
INL _{ADC}	Integral non-linear- ity (INL), End point method	V _{DD} = 3.0 V, external 2.5V reference		±1.2	±3	LSB
MC _{ADC}	No missing codes		11.999 ¹	12		bits
	0	1.25V reference		0.01 ²	0.033 ³	%/°C
GAIN _{ED}	Gain error drift	2.5V reference		0.01 ²	0.03 ³	%/°C
055057	or	1.25V reference		0.2 ²	0.7 ³	LSB/°C
OFFSET _{ED}	Offset error drift	2.5V reference		0.2 ²	0.62 ³	LSB/°C

¹On the average every ADC will have one missing code, most likely to appear around $2048 \pm n*512$ where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic

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at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

²Typical numbers given by abs(Mean) / (85 - 25).

³Max number given by (abs(Mean) + 3x stddev) / (85 - 25).

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.17 (p. 30) and Figure 3.18 (p. 30), respectively.

Figure 3.17. Integral Non-Linearity (INL)

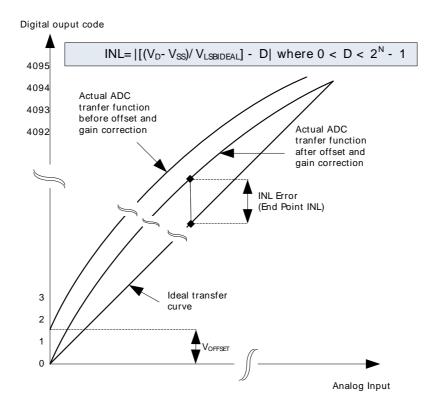
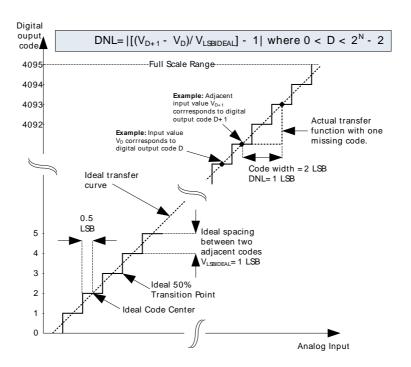


Figure 3.18. Differential Non-Linearity (DNL)



3.10.1 Typical performance

Figure 3.19. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C

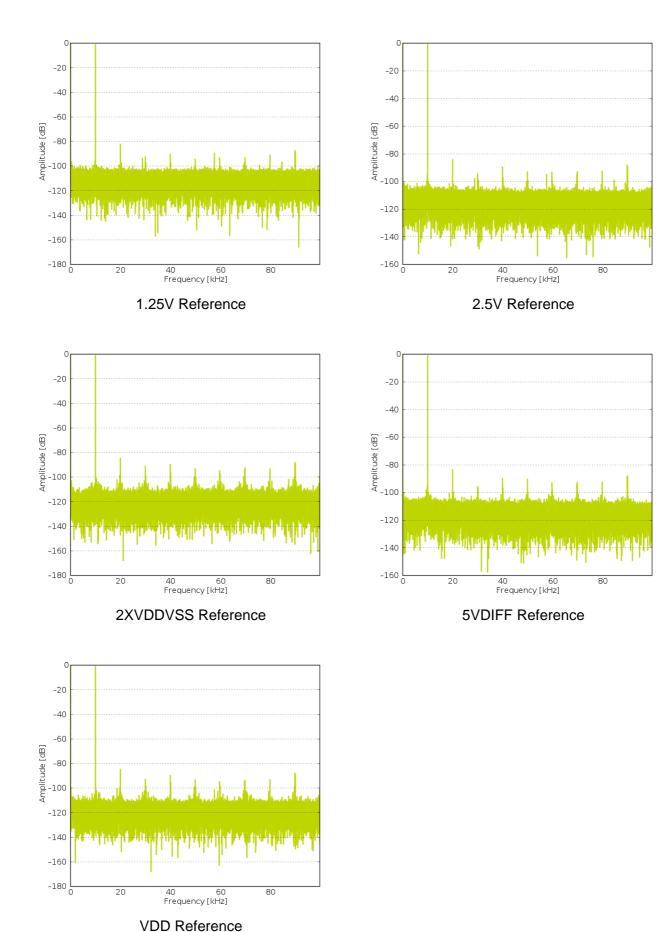
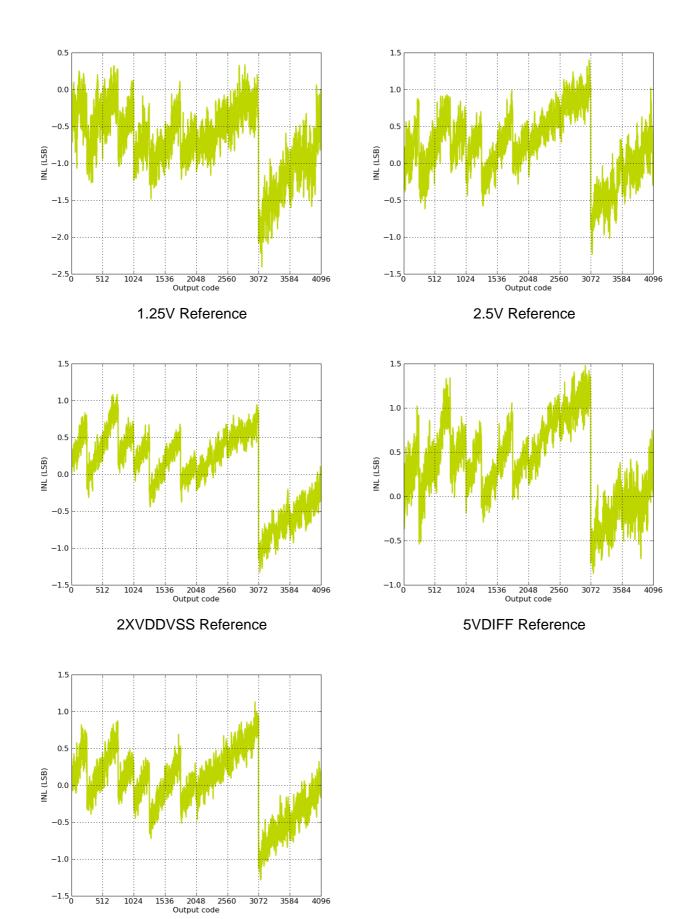


Figure 3.20. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C



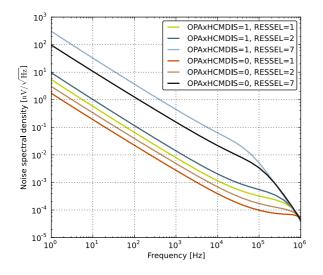
VDD Reference



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		16.36		MHz
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		0.81		MHz
	Gain Bandwidth	OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		0.11		MHz
GBW _{OPAMP}	Product	OPA2 BIASPROG=0xF, HALFBIAS=0x0		2.11		MHz
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		0.72		MHz
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.09		MHz
		BIASPROG=0xF, HALFBIAS=0x0, C _L =75 pF		64		o
PM _{OPAMP}	Phase Margin	BIASPROG=0x7, HALFBIAS=0x1, C _L =75 pF		58		0
		BIASPROG=0x0, HALFBIAS=0x1, C _L =75 pF		58		o
R _{INPUT}	Input Resistance			100		Mohm
5	Load Resistance	OPA0/OPA1	200			Ohm
R _{LOAD}		OPA2	2000			Ohm
		OPA0/OPA1			11	mA
I _{LOAD_DC}	Load Current	OPA2			1.5	mA
		OPAxHCMDIS=0	V _{SS}		V _{DD}	V
V _{INPUT}	Input Voltage	OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V _{DD}	V
		Unity Gain, V _{SS} <v<sub>in<v<sub>DD, OPAxHCMDIS=0</v<sub></v<sub>		6		mV
V _{OFFSET}	Input Offset Voltage	Unity Gain, V _{SS} <v<sub>in<v<sub>DD-1.2, OPAxHCMDIS=1</v<sub></v<sub>		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
		OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		46.11		V/µs
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.21		V/µs
00	Olaus Data	OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/µs
SR _{OPAMP}	Slew Rate	OPA2 BIASPROG=0xF, HALFBIAS=0x0		4.43		V/µs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		1.30		V/µs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/µs



Figure 3.28. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)



3.15 LCD

Table 3.19. LCD

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LCDFR}	Frame rate		30		200	Hz
NUM _{SEG}	Number of seg- ments supported			11×8		seg
V _{LCD}	LCD supply voltage range	Internal boost circuit enabled	2.0		3.8	V
		Display disconnected, stat- ic mode, framerate 32 Hz, all segments on.		250		nA
I _{LCD}	Steady state current consumption.	Display disconnected, quadru- plex mode, framerate 32 Hz, all segments on, bias mode to ONETHIRD in LCD_DISPCTRL register.		550		nA
	Steady state Cur-	Internal voltage boost off		0		μA
ILCDBOOST	rent contribution of internal boost.	Internal voltage boost on, boosting from 2.2 V to 3.0 V.		8.4		μA
		VBLEV of LCD_DISPCTRL register to LEVEL0		3.0		V
		VBLEV of LCD_DISPCTRL register to LEVEL1		3.08		V
		VBLEV of LCD_DISPCTRL register to LEVEL2		3.17		V
V	Depart Voltage	VBLEV of LCD_DISPCTRL register to LEVEL3		3.26		V
V _{BOOST}	Boost Voltage	VBLEV of LCD_DISPCTRL register to LEVEL4		3.34		V
		VBLEV of LCD_DISPCTRL register to LEVEL5		3.43		V
		VBLEV of LCD_DISPCTRL register to LEVEL6		3.52		V
		VBLEV of LCD_DISPCTRL register to LEVEL7		3.6		V

The total LCD current is given by Equation 3.3 (p. 43). I_{LCDBOOST} is zero if internal boost is off.

Total LCD Current Based on Operational Mode and Internal Boost

 $I_{LCDTOTAL} = I_{LCD} + I_{LCDBOOST}$

(3.3)

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. BGA48 PCB Land Pattern

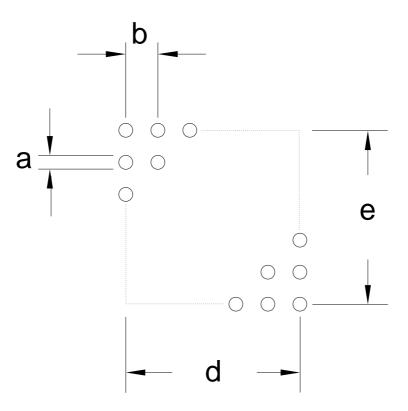


Table 5.1. BGA48 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Row name and column number
а	0.25	r1	А
b	0.50	rn	G
d	3.00	c1	1
е	3.00	cn	7



Figure 5.2. BGA48 PCB Solder Mask

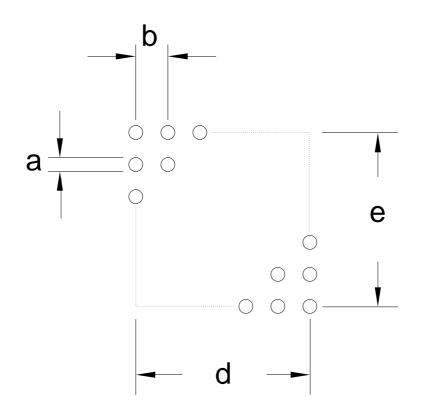


 Table 5.2. BGA48 PCB Solder Mask Dimensions (Dimensions in mm)

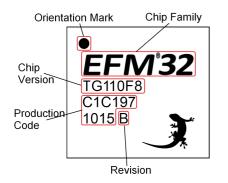
Symbol	Dim. (mm)
а	0.28
b	0.50
d	3.00
е	3.00

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 57).

6.3 Errata

Please see the errata document for EFM32TG825 for description and resolution of device erratas. This document is available in Simplicity Studio and online at: http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit



Initial preliminary release.

B Contact Information

Silicon Laboratories Inc. 400 West Cesar Chavez Austin, TX 78701

Please visit the Silicon Labs Technical Support web page: http://www.silabs.com/support/pages/contacttechnicalsupport.aspx and register to submit a technical support request.

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